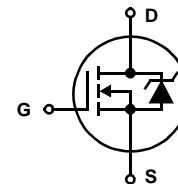
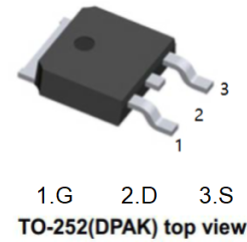


Features

- $V_{DS}(V) = 60V$
- $R_{DS(ON)} < 47m\Omega$ ($V_{GS} = 5V$)
- UIS SOA Rating Curve (Single Pulse)
- Design Optimized for 5V Gate Drives
- Can be Driven Directly from CMOS, NMOS, TTL Circuits
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device



Absolute Maximum Ratings $T_C = 25^\circ C$, Unless Otherwise Specified

Drain to Source Voltage (Note 1)	V_{DS}	60	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	V_{DGR}	60	V
Continuous Drain Current	I_D	16	A
Pulsed Drain Current (Note 3)	I_{DM}	45	A
Gate to Source Voltage	V_{GS}	± 10	V
Maximum Power Dissipation	P_D	60	W
Derate Above $25^\circ C$		0.48	W/ $^\circ C$
Operating and Storage Temperature	T_J, T_{STG}	-55 to 150	$^\circ C$
Maximum Temperature for Soldering			
Leads at 0.063in (1.6mm) from Case for 10s	T_L	300	$^\circ C$
Package Body for 10s, See Techbrief 334	T_{pkg}	260	$^\circ C$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^\circ C$ to $125^\circ C$.

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = 250\text{mA}$, $V_{GS} = 0\text{V}$, Figure 10	60			V	
Gate to Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250\text{mA}$, Figure 9	1		2	V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{V}$, $V_{GS} = 0\text{V}$ $T_C = 150^\circ\text{C}$			1	μA	
					50	μA	
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 10\text{V}$, $V_{DS} = 0\text{V}$			100	nA	
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = 16\text{A}$, $V_{GS} = 5\text{V}$			47	$\text{m}\Omega$	
		$I_D = 16\text{A}$, $V_{GS} = 4\text{V}$			56	$\text{m}\Omega$	
Turn-On Time	$t_{(ON)}$	$V_{DD} = 25\text{V}$, $I_D = 8\text{A}$, $V_{GS} = 5\text{V}$, $R_{GS} = 12.5\Omega$ Figures 15, 16			60	ns	
Turn-On Delay Time	$t_{d(ON)}$			14		ns	
Rise Time	t_r			30		ns	
Turn-Off Delay Time	$t_{d(OFF)}$			42		ns	
Fall Time	t_f			14		ns	
Turn-Off Time	$t_{(OFF)}$					100	ns
Total Gate Charge	$Q_{g(TOT)}$		$V_{GS} = 0\text{V}$ to 10V	$V_{DD} = 40\text{V}$, $I_D = 16\text{A}$, $R_L = 2.5\Omega$ Figures 17, 18		80	nC
Gate Charge at 5V	$Q_{g(5)}$	$V_{GS} = 0\text{V}$ to 5V			45	nC	
Threshold Gate Charge	$Q_{g(TH)}$	$V_{GS} = 0\text{V}$ to 1V			3	nC	
Thermal Resistance Junction to Case	$R_{\theta JC}$				2.083	$^\circ\text{C/W}$	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$				100	$^\circ\text{C/W}$	

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 16\text{A}$			1.5	V
Diode Reverse Recovery Time	t_{rr}	$I_{SD} = 16\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$			125	ns

NOTES:

2. Pulse Test: Pulse Width $\leq 300\text{ms}$, Duty Cycle $\leq 2\%$.
3. Repetitive Rating: Pulse Width limited by max junction temperature.

Typical Performance Curves Unless Otherwise Specified

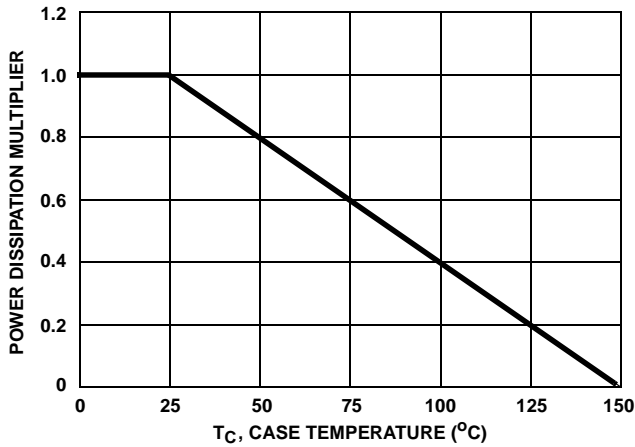


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

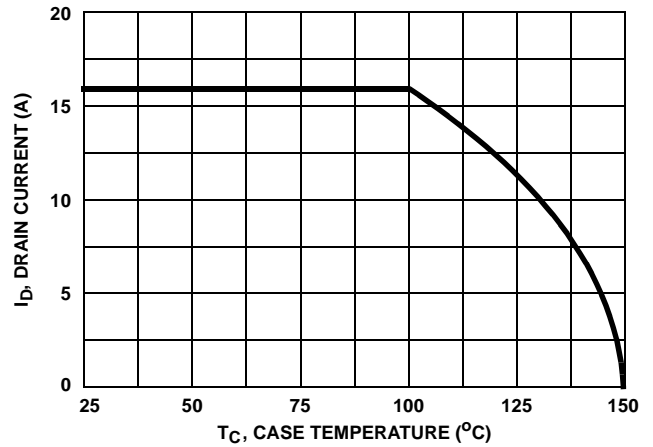


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

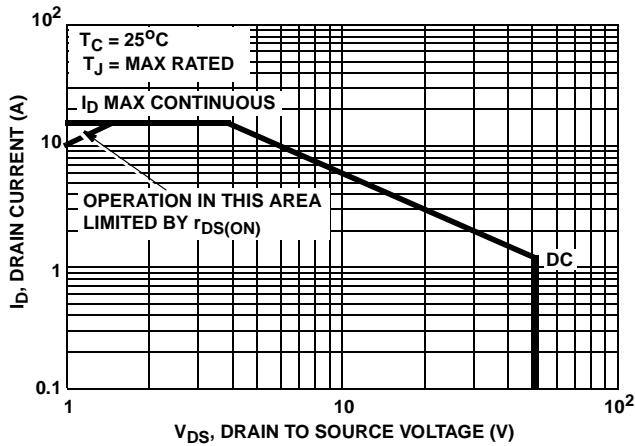


FIGURE 3. FORWARD BIAS SAFE OPERATING AREA

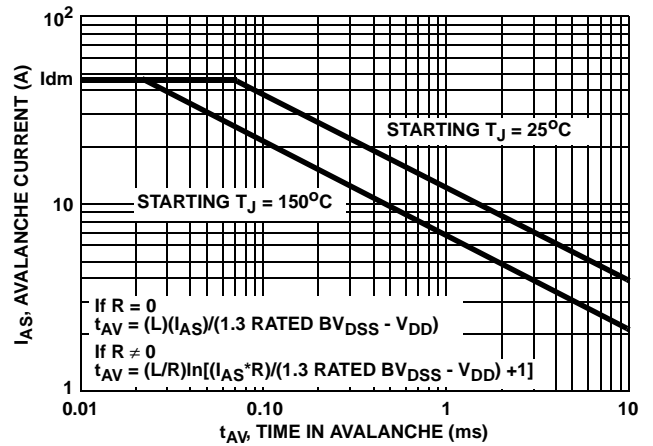


FIGURE 4. UNCLAMPED INDUCTIVE SWITCHING SOA (SINGLE PULSE UIS SOA)

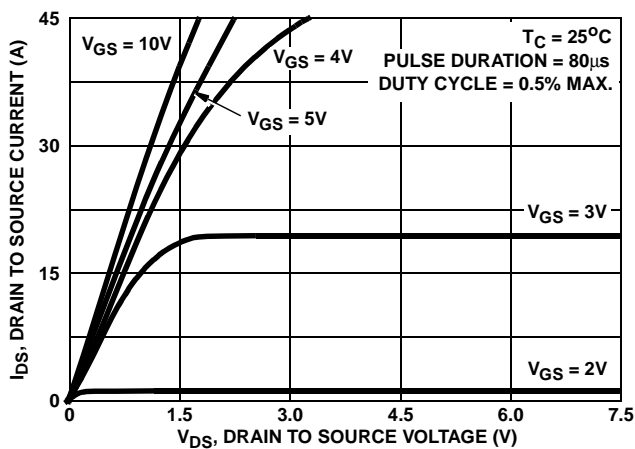


FIGURE 5. SATURATION CHARACTERISTICS

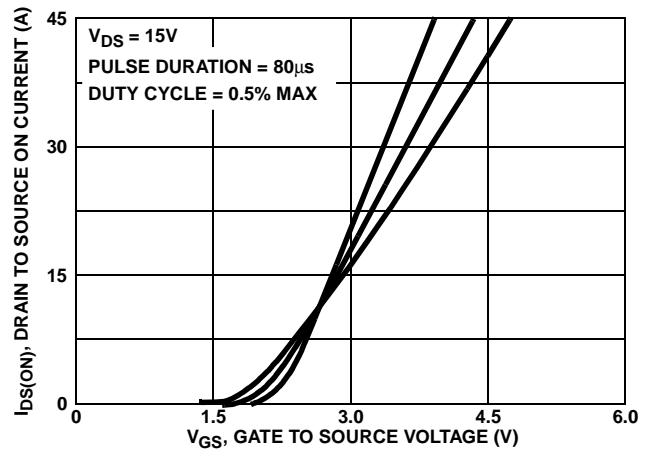


FIGURE 6. TRANSFER CHARACTERISTICS

Typical Performance Curves Unless Otherwise Specified

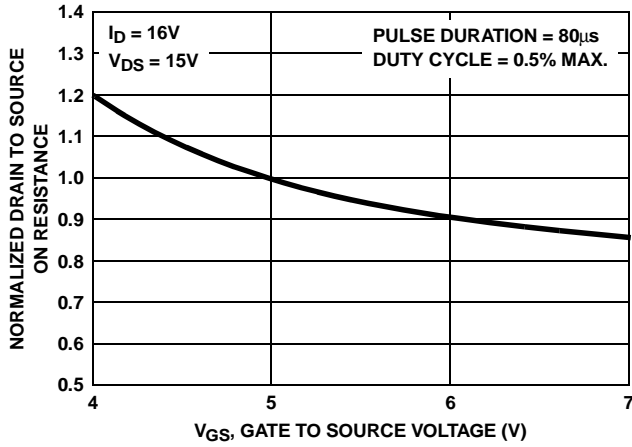


FIGURE 7. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

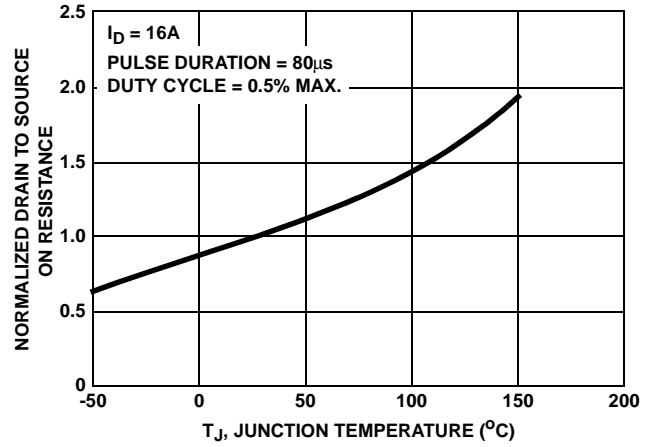


FIGURE 8. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

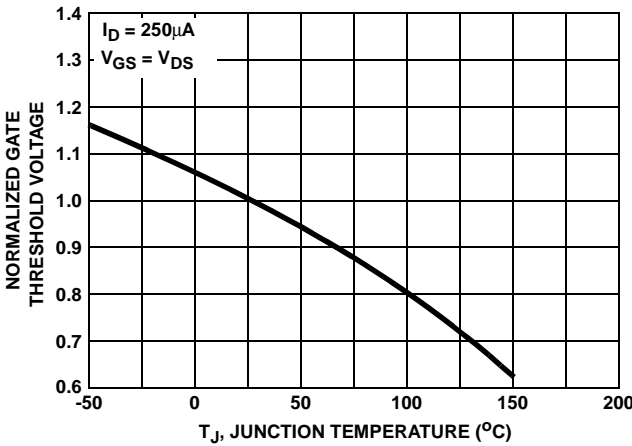


FIGURE 9. NORMALIZED GATE THRESHOLD vs JUNCTION TEMPERATURE

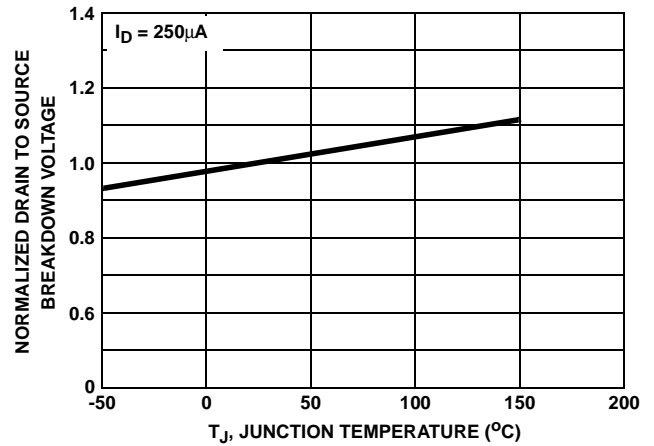


FIGURE 10. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

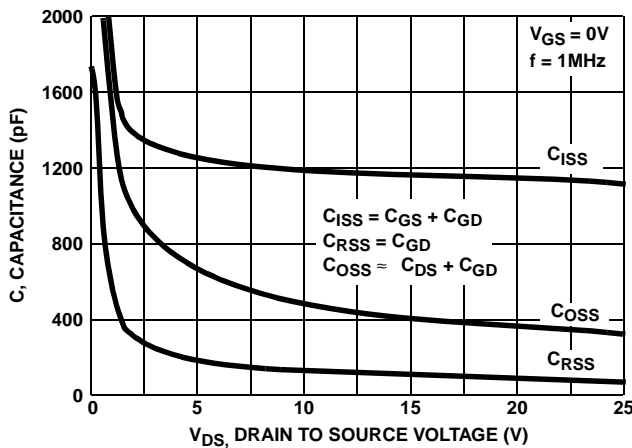


FIGURE 11. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

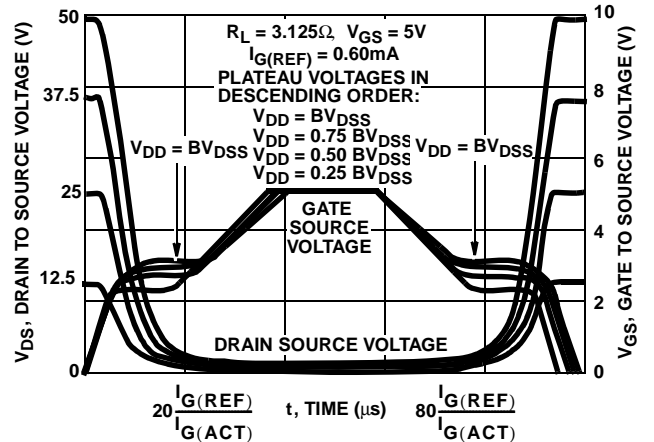


FIGURE 12. NORMALIZED SWITCHING WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms

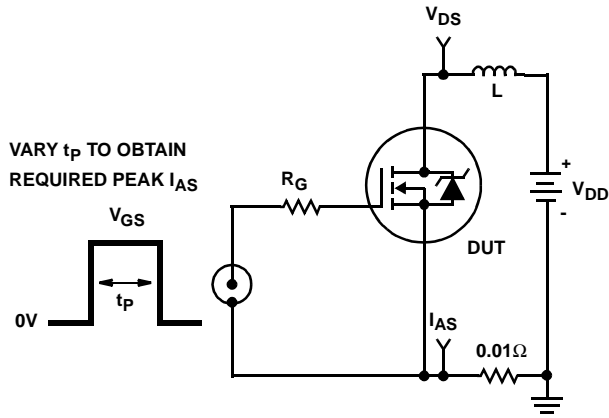


FIGURE 13. UNCLAMPED ENERGY TEST CIRCUIT

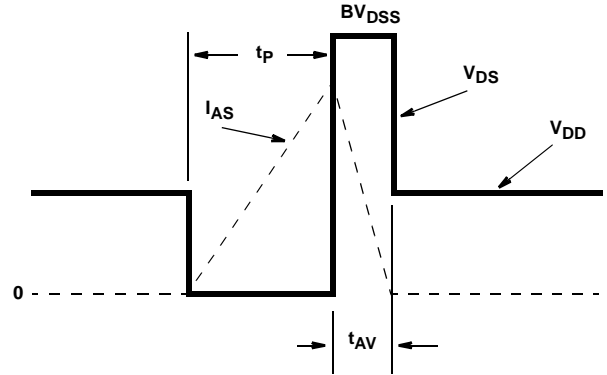


FIGURE 14. UNCLAMPED ENERGY WAVEFORMS

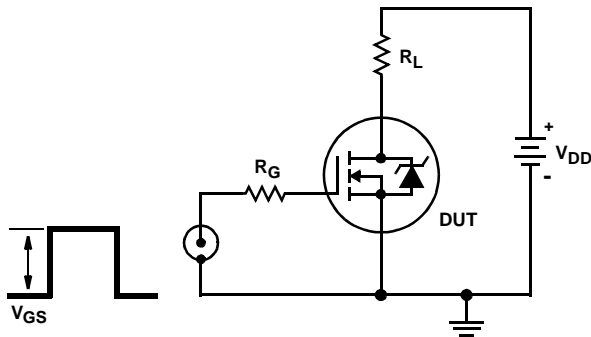


FIGURE 15. SWITCHING TIME TEST CIRCUIT

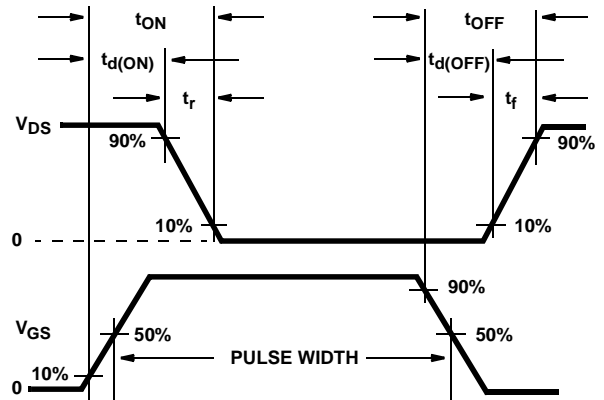


FIGURE 16. RESISTIVE SWITCHING WAVEFORMS

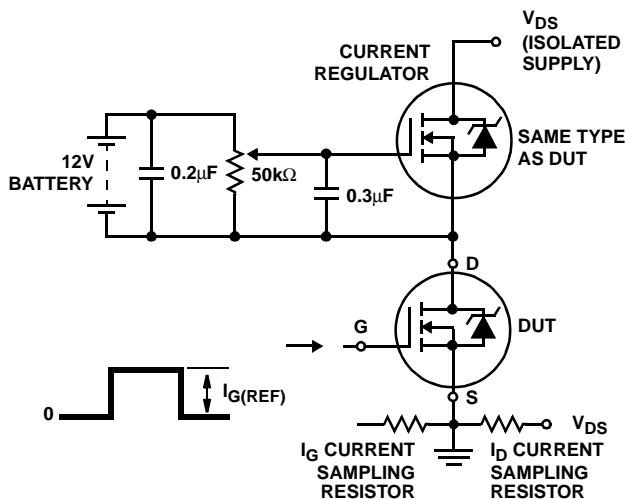


FIGURE 17. GATE CHARGE TEST CIRCUIT

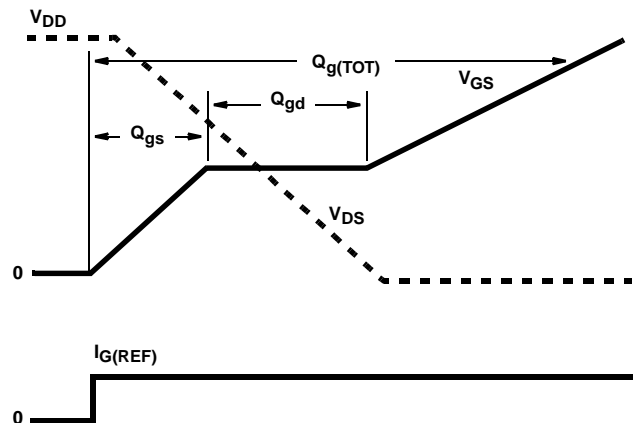
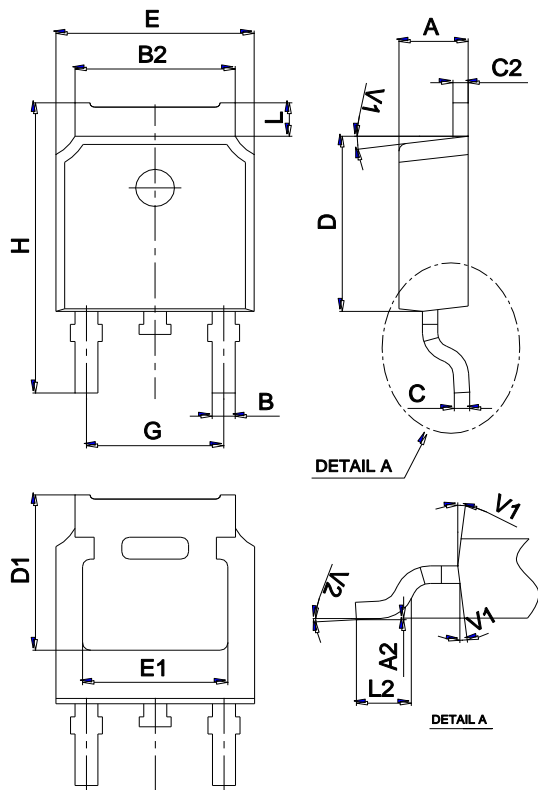


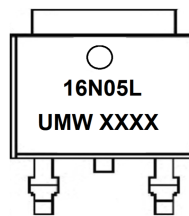
FIGURE 18. GATE CHARGE WAVEFORMS

Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2		0°	6°	0°		6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW RFD16N05LSM9A	TO-252	2500	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)